L Number	Hits	Search Text	DB	Time stamp
12	528	438/687,618,633,627,643,687.CCLS. and ((barrier or diffus$5) adj (layer or film)) and (expos$3 or treat$6) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 08:03
13	3489	438/$.CCLS. and ((barrier or diffus$5) adj (layer or film)) and (expos$3 or treat$6) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 08:03
15	498	438/687,618,633,627,643,687.CCLS. and (barrier adj (layer or film)) and (expos$3 or treat$6) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 08:04
14	239	438/687,618,633,627,643,687.CCLS. and (barrier adj (layer or film)) and ((expos$3 or treat$6) same ((reduc$3 adj gases) or (hydrogen or ("H.sub.2")))) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 08:04
-	833	438/618	USPAT; EPO; JPO; DERWENT	2003/03/10 10:42
-	672	438/633	USPAT; EPO; JPO; DERWENT	2001/12/17 14:40
-	45384	barrier adj (layer or film)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:06
-	1055	(barrier adj (layer or film)) and (reduc$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2004/03/02 08:58
-	237	((barrier adj (layer or film)) and (reduc$4 adj (gas or agent or chemical))) and (metal adj (film or layer))	USPAT; EPO; JPO; DERWENT	2001/12/18 08:17
-	5	(barrier adj (layer or film)) and (first adj reduc$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:56
-	0	((barrier adj (layer or film)) and (first adj reduc$4 adj (gas or agent or chemical))) and (metal adj (film or layer))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:53
-	0	(((barrier adj (layer or film)) and (reduc$4 adj (gas or agent or chemical))) and (metal adj (film or layer))) and (second adj reduc$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:55
-	237	(((barrier adj (layer or film)) and (reduc$4 adj (gas or agent or chemical))) and (metal adj (film or layer))) and (reduc$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:55
-	163	(first adj reduc$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:58
-	92	((first adj reduc$4 adj (gas or agent or chemical))) and (second adj reduc$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 15:01
-	6	(((first adj reduc$4 adj (gas or agent or chemical))) and (second adj reduc$4 adj (gas or agent or chemical))) and semiconductor	USPAT; EPO; JPO; DERWENT	2001/12/17 15:01
-	683	438/627	USPAT; EPO; JPO; DERWENT	2001/12/17 15:31
-	1178	438/643	USPAT; EPO; JPO; DERWENT	2002/01/02 14:19
-	20851	(((diffus$6 adj barrier) or prevent$10) adj (layer or film))	USPAT; EPO; JPO; DERWENT	2001/12/18 14:01

-	394	((((diffus$6 adj barrier) or prevent$10) adj (layer or film))) and (reduc$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/18 08:17
-	96	(((((diffus$6 adj barrier) or prevent$10) adj (layer or film))) and (reduc$4 adj (gas or agent or chemical))) and (metal adj (film or layer))	USPAT; EPO; JPO; DERWENT	2001/12/18 12:54
-	20851	(((diffus$6 adj barrier) or prevent$10) adj (layer or film))	USPAT; EPO; JPO; DERWENT	2001/12/18 14:02
-	3447	(((diffus$6 adj barrier) or (diffus$6 adj prevent$10)) adj (layer or film))	USPAT; EPO; JPO; DERWENT	2001/12/18 14:04
-	40	((((diffus$6 adj barrier) or prevent$10) adj (layer or film))) and (first adj anneal$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:07
-	0	(((((diffus$6 adj barrier) or prevent$10) adj (layer or film))) and (first adj anneal$5)) and (second adj aneal$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:08
-	45418	barrier adj (layer or film)	USPAT; EPO; JPO; DERWENT	2003/03/07 13:53
-	147	(barrier adj (layer or film)) and (first adj anneal$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:08
-	0	((barrier adj (layer or film)) and (first adj anneal$5)) and (second adj aneal$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:21
-	483098	plug or interconnection	USPAT; EPO; JPO; DERWENT	2001/12/18 14:23
-	108014	metal adj (layer or film)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:24
-	18975	(metal adj (layer or film)) and (plug or interconnect$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:25
-	3544	((metal adj (layer or film)) and (plug or interconnect$5)) and anneal$5	USPAT; EPO; JPO; DERWENT	2001/12/18 14:25
-	56	(((metal adj (layer or film)) and (plug or interconnect$5)) and anneal$5) and (reduc$3 adj atmosphere)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:30
-	6	((barrier adj (layer or film)) and (first adj anneal$5)) and (reduc$3 adj atmosphere)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:31
-	40	((((metal adj (layer or film)) and (plug or interconnect$5)) and anneal$5) and (reduc$3 adj atmosphere)) and semiconductor	USPAT; EPO; JPO; DERWENT	2001/12/18 14:37
-	6	(((barrier adj (layer or film)) and (first adj anneal$5)) and (reduc$3 adj atmosphere)) and semiconductor	USPAT; EPO; JPO; DERWENT	2001/12/18 14:36
-	5	(("5116463") or ("6207222") or ("6197688") or ("6191031") or ("6143646")).PN.	USPAT	2004/03/02 12:52
-	562	438/687	USPAT; EPO; JPO; DERWENT	2004/02/20 13:52
-	55733	barrier adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 07:56
-	489	(barrier adj (layer or film)) and (reduc$3 adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:01

-	160	((barrier adj (layer or film)) and (reduc$3 adj (gas or ambient))) and (metal adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:03
-	3	(((barrier adj (layer or film)) and (reduc$3 adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:08
-	222	(barrier adj (layer or film)) and (reduc$3 adj (gas or ambient)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:05
-	3	((((barrier adj (layer or film)) and (reduc$3 adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 13:59
-	113	(((barrier adj (layer or film)) and (reduc$3 adj (gas or ambient))) and (metal adj (layer or film))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:06
-	28226	(barrier adj (layer or film)) and (reduc$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:03
-	6490	((barrier adj (layer or film)) and (reduc$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:05
-	222	((barrier adj (layer or film)) and (reduc$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (reduc$3 adj (gas or ambient)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:07
-	8105	((barrier adj (layer or film)) and (reduc$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:07
-	3403	(((barrier adj (layer or film)) and (reduc$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:07
-	99	(((barrier adj (layer or film)) and (reduc$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:07
-	99	((((barrier adj (layer or film)) and (reduc$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))) and (second adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:10
-	92	(((((barrier adj (layer or film)) and (reduc$3 or (hygrogen or ("H.sub.2")) adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))) and (second adj (gas or ambient))) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:10
-	25099	barrier adj (layer or film)	USPAT	2003/03/10 07:56
-	7320	(barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))))	USPAT	2003/03/10 08:01

–	3856	((barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor	USPAT	2003/03/10 08:02
–	1694	(((barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film))	USPAT	2003/03/10 08:03
–	303	(((barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))	USPAT	2003/03/10 08:04
–	60	((((barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2")))))) and semiconductor) and (metal adj (layer or film))) and (second adj gas)	USPAT	2003/03/10 08:05
–	9	((((barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2")))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas)	USPAT	2004/02/20 13:52
–	2	(("5665659") or ("5953634")).PN.	USPAT	2004/02/23 09:53
–	1	("6475902").PN.	USPAT	2003/11/17 07:10
–	1	("20020009872").PN.	US-PGPUB	2003/11/14 16:12
–	3	(("20020022354") or ("6248633") or ("6303959")).PN.	USPAT; US-PGPUB	2003/11/17 06:46
–	10	(((((barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas)	USPAT	2004/02/20 13:53
–	1661	438/687	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:52
–	1884	438/618	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:52
–	1281	438/633	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:52
–	1407	438/627	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:53
–	1772	438/643	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:53
–	1661	438/687	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:53

–	2	438/687,618,633,627,643,687.CCLS. and ((((barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/02 13:03
–	8	438/$.CCLS. and ((((barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:58
–	8	257/$.CCLS. and ((((barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:59
–	11	((((barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:59
–	5	("5139825" | "5178911" | "5856236" | "5900498" | "5908947").PN.	USPAT	2004/02/23 08:02
–	2508	(barrier adj (layer or film)) and (reduc$4) and (metal adj (layer or film)) and (treat$6 or ((post adj treat$6) or (post-treat$6) or (posttreat$6)))	USPAT; EPO; JPO; DERWENT	2004/03/02 09:01
–	2198	(barrier adj (layer or film)) and (reduc$4) and (metal adj (layer or film)) and (treat$6 or ((post adj treat$6) or (post-treat$6) or (posttreat$6))) and @ad<=20010417	USPAT; EPO; JPO; DERWENT	2004/03/02 09:02
–	1612	semiconductor and (barrier adj (layer or film)) and (reduc$4) and (metal adj (layer or film)) and (treat$6 or ((post adj treat$6) or (post-treat$6) or (posttreat$6))) and @ad<=20010417	USPAT; EPO; JPO; DERWENT	2004/03/02 09:12
–	1416	(semiconductor and (barrier adj (layer or film)) and (reduc$4) and (metal adj (layer or film)) and (treat$6 or ((post adj treat$6) or (post-treat$6) or (posttreat$6))) and @ad<=20010417) and expos$6	USPAT; EPO; JPO; DERWENT	2004/03/02 09:13
–	1416	((semiconductor and (barrier adj (layer or film)) and (reduc$4) and (metal adj (layer or film)) and (treat$6 or ((post adj treat$6) or (post-treat$6) or (posttreat$6))) and @ad<=20010417) and expos$6) and reduc$6	USPAT; EPO; JPO; DERWENT	2004/03/02 09:15
–	1	("5,953,634").PN.	USPAT	2004/03/02 12:53
–	1	("5,665,659").PN.	USPAT	2004/03/02 12:53
–	2	438/687,618,633,627,643,687.CCLS. and ((((barrier adj (layer or film)) and ((expos$3 or anneal$5) and ((reduc$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 08:00